

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _A = +25°C
240V	11Ω @ V _{GS} = 10V	0.27A
	12Ω @ V _{GS} = 4.5V	0.26A

Description

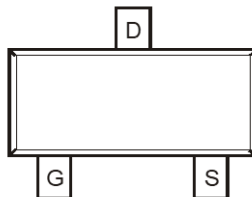
This new generation MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

Applications

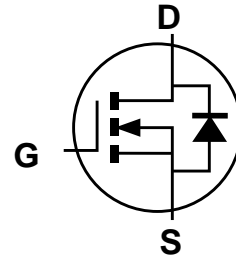
- DC-DC converters
- Power-management functions
- Battery-operated systems and solid-state relays
- Drivers: relays, solenoids, lamps, hammers, displays, memories, transistors, etc.



Top View



Top View
Pin Configuration



Equivalent Circuit

Features and Benefits

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface-Mount Package
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.**
<https://www.diodes.com/quality/product-definitions/>
- **An automotive-compliant part is available under separate datasheet ([DMN24H11DSQ](#))**

Mechanical Data

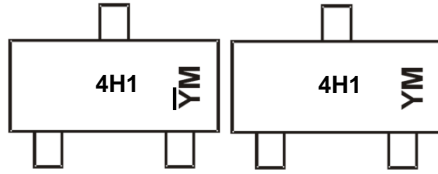
- Package: SOT23
- Package Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Solderable per MIL-STD-202, Method 208 Lead Free Plating (Matte Tin Finish Annealed over Alloy 42 Leadframe).
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)

Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMN24H11DS-7	SOT23	3,000	Tape & Reel
DMN24H11DS-13	SOT23	10,000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



4H1 = Product Type Marking Code
 YM = Date Code Marking for SAT (Shanghai Assembly/ Test Site)
 Y̅M = Date Code Marking for CAT (Chengdu Assembly/ Test Site)
 Y or Y̅ = Year (ex: K = 2023)
 M = Month (ex: 9 = September)

Date Code Key

Year	2014	-	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032
Code	B	-	K	L	M	N	P	R	S	T	U	V

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	240	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	I _D	Steady State	A
		T _A = +25°C T _A = +70°C	
Pulsed Drain Current (10µs Pulse, Duty Cycle ≤1%) (Note 5)	I _{DM}	0.8	A
Maximum Body Diode Continuous Current (Note 6)	I _S	0.27	A
Pulsed Body Diode Continuous Current (10µs Pulse, Duty Cycle ≤1%) (Note 5)	I _{SM}	0.8	A
Peak Diode Recovery dv/dt	dv/dt	6.0	V/ns

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation	P _D	(Note 5)	0.75
		(Note 6)	1.2
Thermal Resistance, Junction to Ambient	R _{θJA}	(Note 5)	166
		(Note 6)	104
Thermal Resistance, Junction to Case	R _{θJC}	35	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	240	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	100	nA	V _{DS} = 240V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	1.0	2.0	3.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	3.7	11	Ω	V _{GS} = 10V, I _D = 0.3A
		—	4.0	12		V _{GS} = 4.5V, I _D = 0.2A
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 0.1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	76.8	—	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	6.9	—		
Reverse Transfer Capacitance	C _{rss}	—	4.1	—		
Gate Resistance	R _G	—	17	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge	Q _g	—	3.7	—	nC	V _{DS} = 192V, V _{GS} = 10V, I _D = 0.1A
Gate-Source Charge	Q _{gs}	—	0.3	—		
Gate-Drain Charge	Q _{gd}	—	2.1	—		
Turn-On Delay Time	t _{D(on)}	—	4.8	—	ns	V _{DS} = 120V, I _D = 0.1A, V _{GS} = 10V, R _G = 6.0Ω
Turn-On Rise Time	t _r	—	4.7	—		
Turn-Off Delay Time	t _{D(off)}	—	17.5	—		
Turn-Off Fall Time	t _f	—	102.3	—		
Reverse Recovery Time	t _{rr}	—	45.6	—	ns	V _R = 100V, I _F = 1.0A, di/dt = 100A/μs
Reverse Recovery Charge	Q _{rr}	—	51.6	—	nC	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

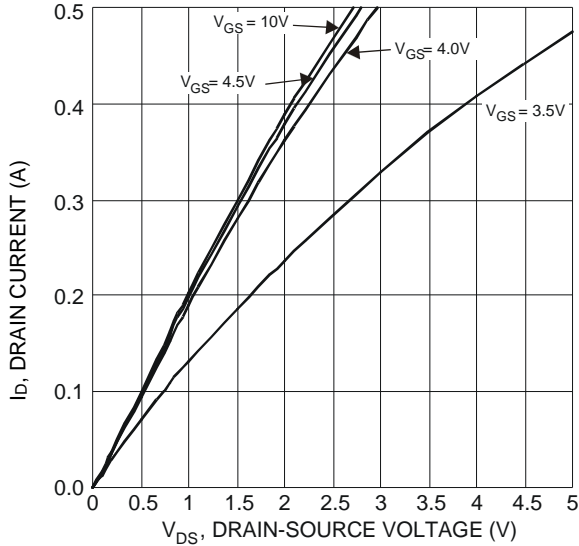


Figure 1 Typical Output Characteristics

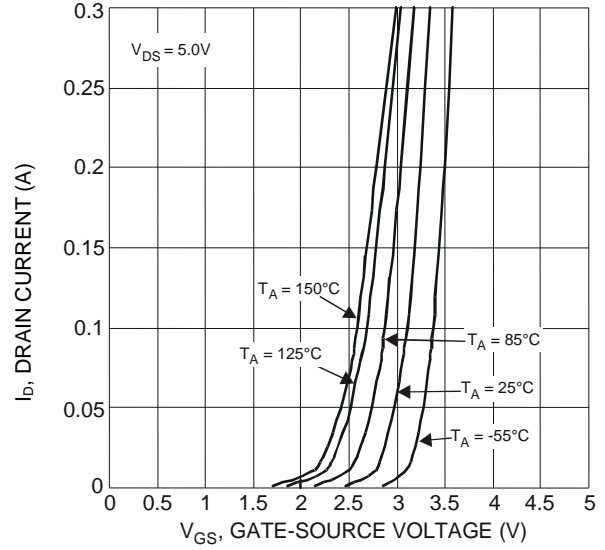


Figure 2 Typical Transfer Characteristics

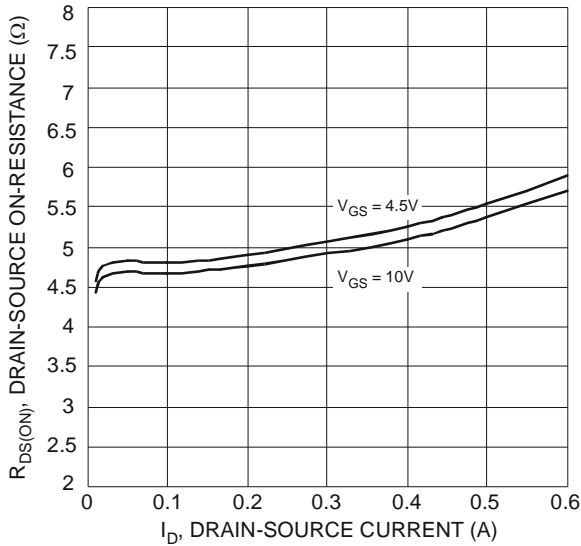


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

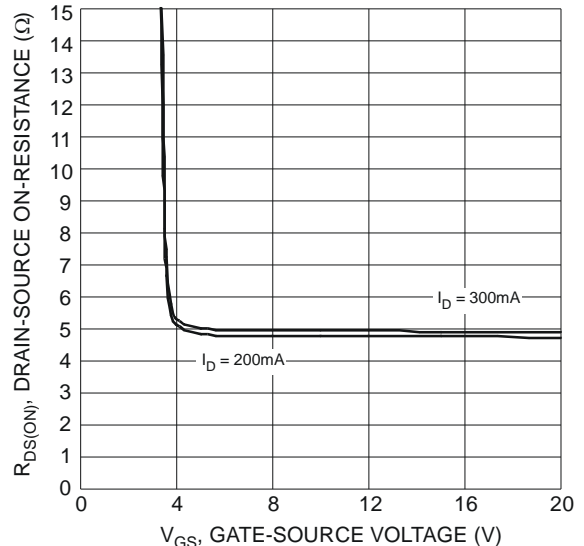


Figure 4 Typical Transfer Characteristics

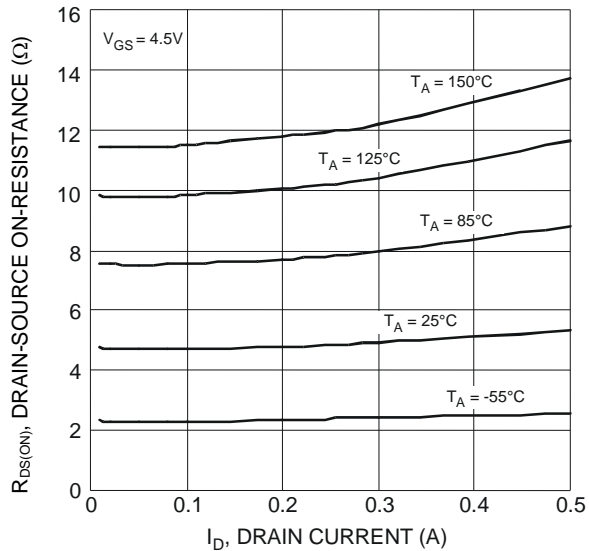


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

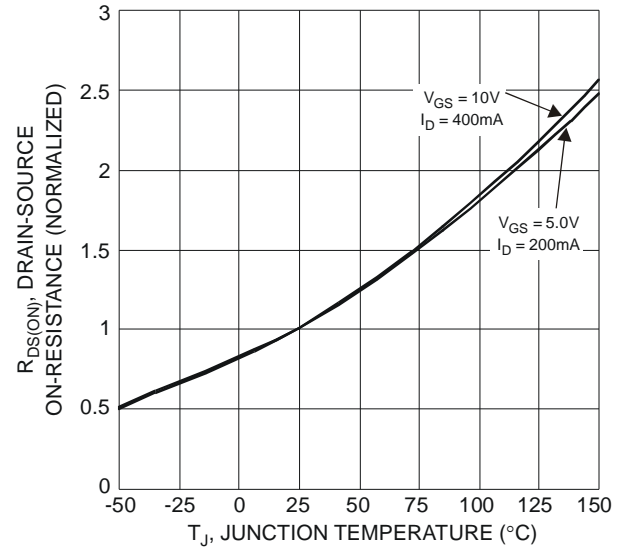


Figure 6 On-Resistance Variation with Temperature

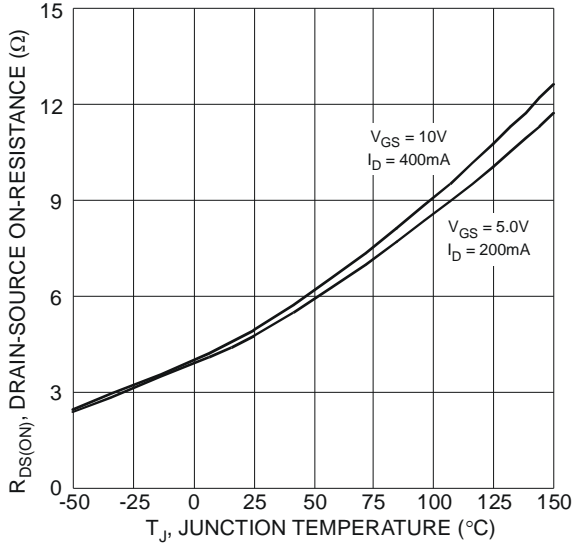


Figure 7 On-Resistance Variation with Temperature

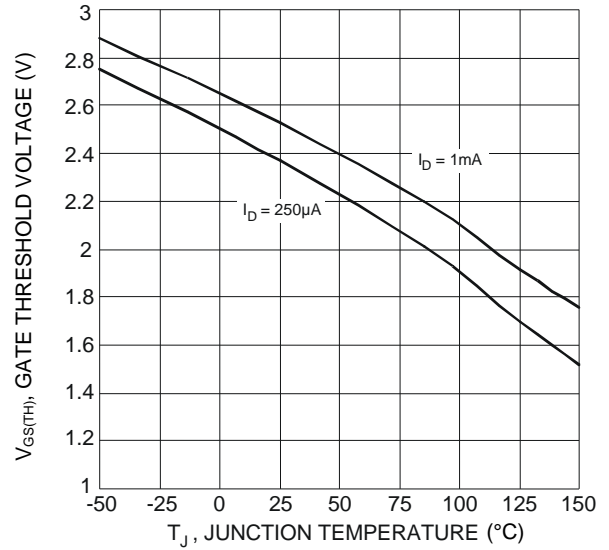


Figure 8 Gate Threshold Variation vs. Junction Temperature

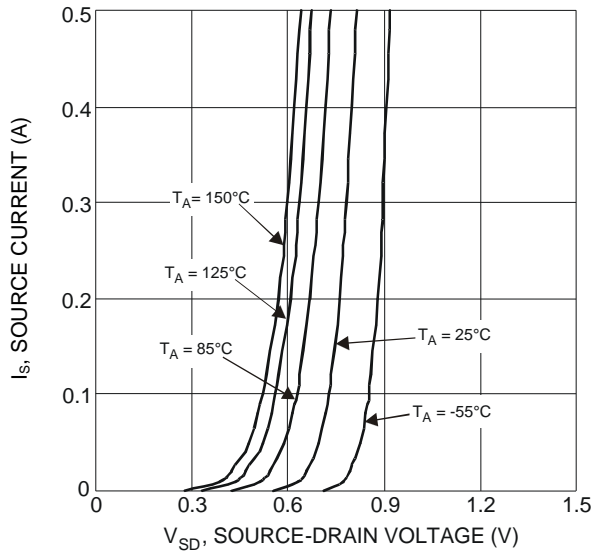


Figure 9 Diode Forward Voltage vs. Current

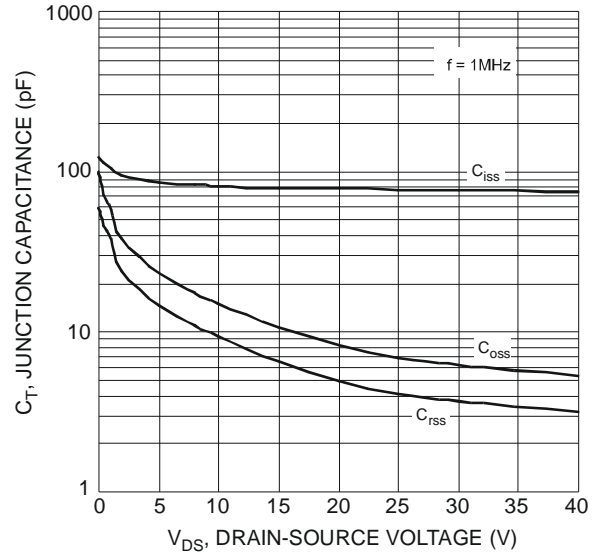


Figure 10 Typical Junction Capacitance

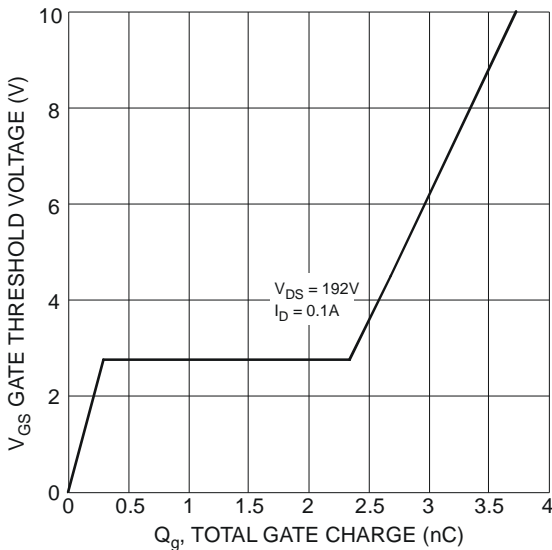


Figure 11 Gate Charge

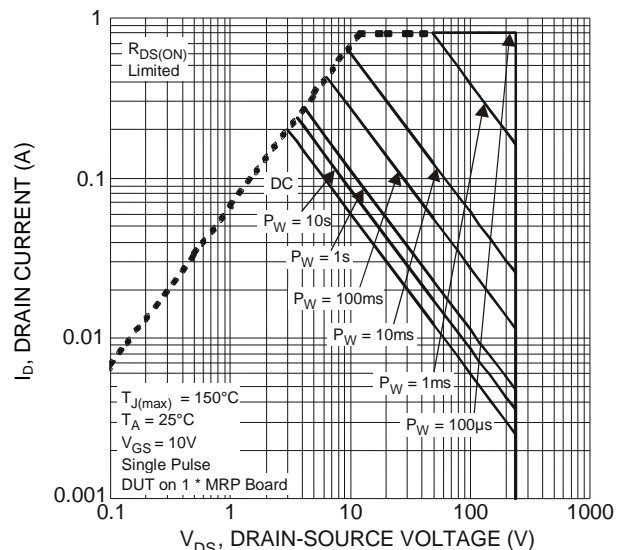


Figure 12 SOA, Safe Operation Area

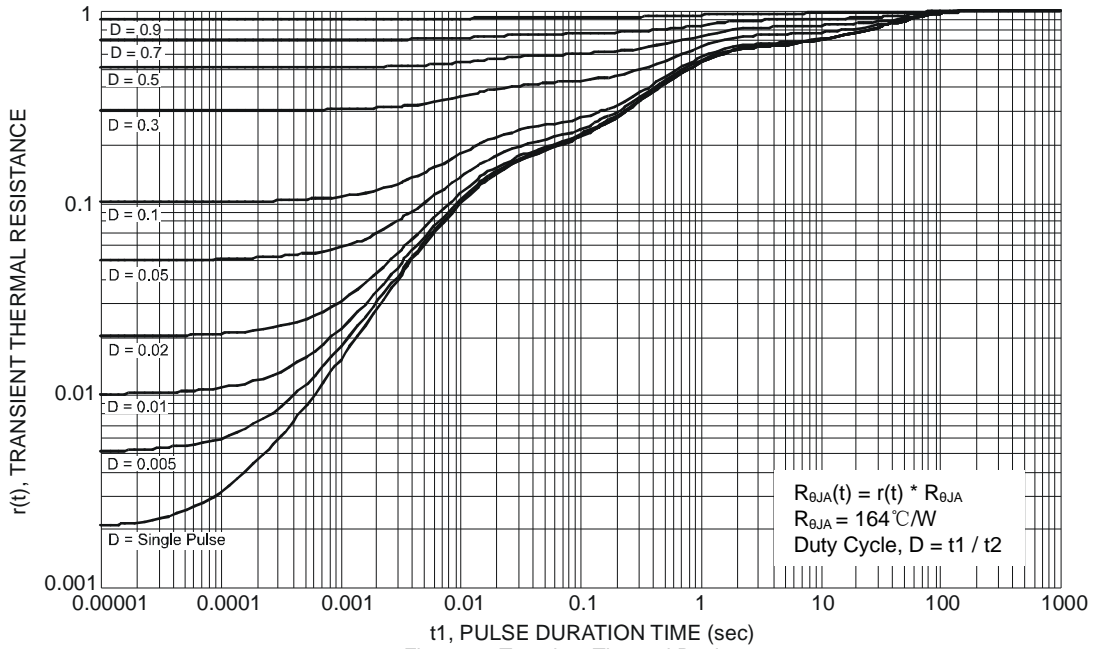
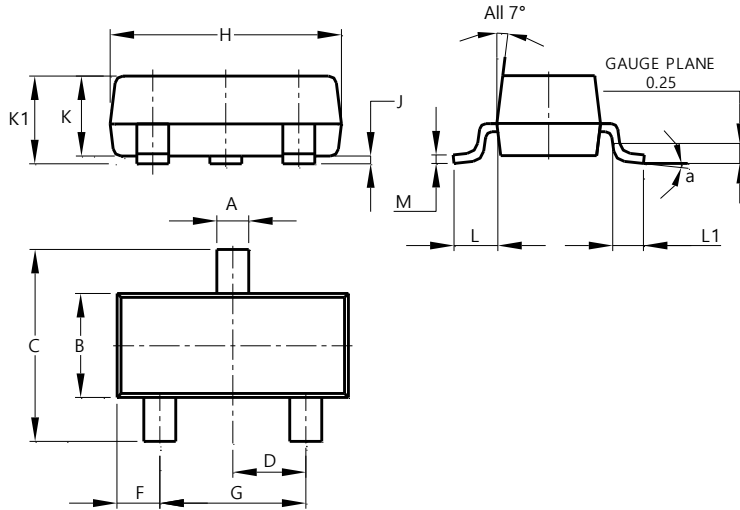


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23

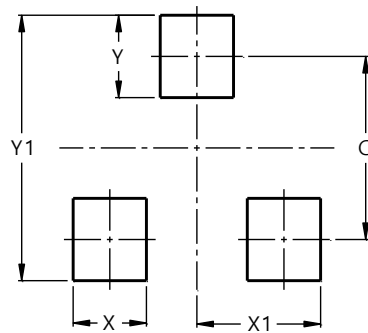


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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